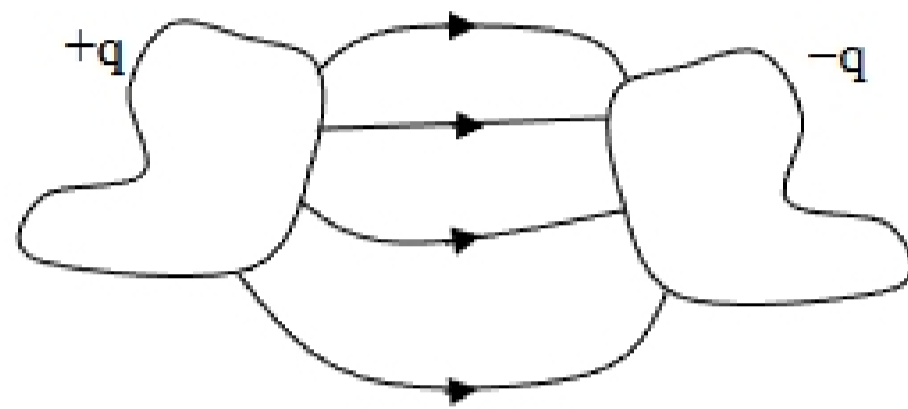


Capacitance

Disclaimer: These lecture notes are not meant to replace the course textbook. The content may be incomplete. Some topics may be unclear. These notes are only meant to be a study aid and a supplement to your own notes. Please report any inaccuracies to the professor.



A set of conductors can store electric charge. The net charge $Q=0=q-q$, but the magnitude of charge on each conductor is $|q|$.

This charge q is proportional to the potential difference between the conductors:

$$q = C\Delta V \quad \Delta V = V_+ - V_- \equiv V$$

$$q = CV$$

The constant of proportionality between charge and potential difference is C ≡capacitance. Unit is Farad (F) ≡ Coulomb/Volt.

$$1\mu\text{F} = 10^{-6} \text{ F}$$

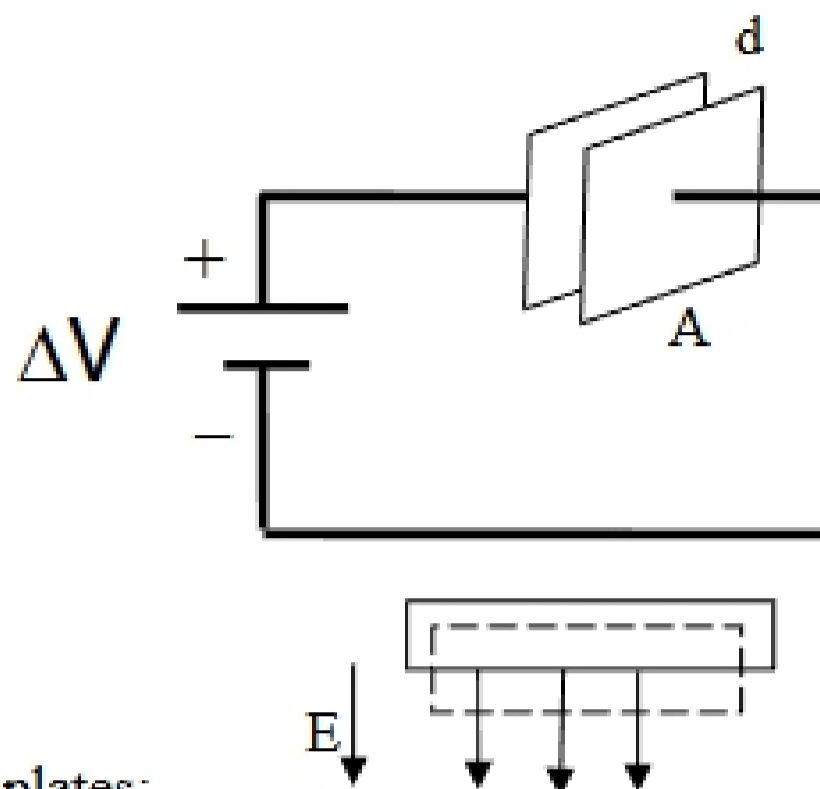
$$1\text{pF} = 10^{-12} \text{ F}$$

To set up a potential difference between 2 conductors requires an electric “pump”, such as a battery (see next chapter).



A larger capacitance implies that a large charge q is stored for the same potential difference V .

Capacitance depends only on the geometry of the conductors, not the charge q or voltage V . We can see this through examples.

Parallel Plate Capacitor

Consider the top view of the 2 plates:

Create a Gaussian surface (box) that extends inside and outside one of the conductor surfaces.

$$\text{Gauss' Law} \Rightarrow \Phi = \oint_s \mathbf{E} \cdot d\mathbf{A} = \frac{q_{\text{enc}}}{\epsilon_0}$$

$\mathbf{E} = 0$ inside a conductor

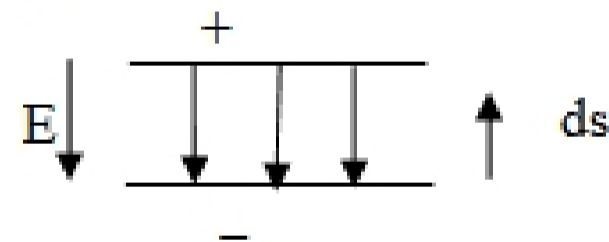
$\mathbf{E} \cdot d\mathbf{A} = 0$ on left/right edges

$|\mathbf{E}| \neq 0$ on front outside face only

$$\Rightarrow \Phi = \oint_s \mathbf{E} \cdot d\mathbf{A} = EA = \frac{q_{\text{enc}}}{\epsilon_0}$$

$$\Rightarrow q = \epsilon_0 EA$$

The electric potential difference between the 2 plates is given by:



$$\Delta V = V_+ - V_- = -\int_-^+ \mathbf{E} \cdot ds \quad \mathbf{E} \cdot ds = -|\mathbf{E}| ds \quad \text{opposite directions}$$

$$\Delta V = |\mathbf{E}| d$$

$$\Rightarrow |\mathbf{E}| = \frac{\Delta V}{d}$$

So for parallel plates:

$$q = \epsilon_0 EA = \epsilon_0 \frac{\Delta V}{d} A = \left(\epsilon_0 \frac{A}{d} \right) \Delta V$$

$$q = C \Delta V$$

$$\Rightarrow \boxed{C = \epsilon_0 \frac{A}{d}} \quad \epsilon_0 = 8.85 \times 10^{-12} \frac{\text{C}^2}{\text{Nm}^2} = 8.85 \text{ pF/m}$$

Cylindrical Capacitor (Cable)

Let inner conductor have radius a , and outer radius b .

Take Gaussian surface as cylinder between conductors ($\mathbf{E}=0$ inside conductors).

$$\Phi = \oint_s \mathbf{E} \cdot d\mathbf{A} = \frac{q_{\text{enc}}}{\epsilon_0}$$

$$\Rightarrow E 2\pi r L \epsilon_0 = q \quad \mathbf{E} \cdot d\mathbf{A} = 0 \text{ on cylinder ends}$$

$$\Rightarrow E = \frac{q}{2\pi\epsilon_0 L r}$$

$$\Delta V = V_+ - V_- = -\int_-^+ \mathbf{E} \cdot d\mathbf{s} \quad \mathbf{E} \cdot d\mathbf{s} = -|\mathbf{E}| ds \quad \text{opposite directions, but } ds = -dr \text{ opposite again}$$

$$\Delta V = -\int_-^+ |\mathbf{E}| dr = \int_a^b |\mathbf{E}| dr = \int_a^b \frac{q}{2\pi\epsilon_0 L r} dr$$

$$\Delta V = \frac{q}{2\pi\epsilon_0 L} \ln \frac{b}{a}$$

$$\Rightarrow q = \left(\frac{2\pi\epsilon_0 L}{\ln b/a} \right) \Delta V$$

$$\Rightarrow C = \frac{2\pi\epsilon_0 L}{\ln b/a}$$

Spherical Capacitor

Let inner sphere have radius a , and outer radius b .

Take Gaussian surface as sphere between conductors ($\mathbf{E}=0$ inside conductors).

$$\text{Gauss' Law} \Rightarrow |\mathbf{E}| = K \frac{q}{r^2} \quad a < r < b$$

$$\Delta V = V_+ - V_- = -\int_-^+ \mathbf{E} \cdot d\mathbf{s} \quad \mathbf{E} \cdot d\mathbf{s} = -|\mathbf{E}| ds \quad \text{opposite directions, but } ds = -dr \text{ opposite again}$$

$$\Delta V = -\int_-^+ |\mathbf{E}| dr = \int_a^b |\mathbf{E}| dr = \int_a^b Kq \frac{dr}{r^2}$$

$$\Delta V = Kq \left(-\frac{1}{r} \right) \Big|_a^b = Kq \left(\frac{1}{a} - \frac{1}{b} \right)$$

$$\Rightarrow q = \left(\frac{1}{K} \frac{ab}{b-a} \right) \Delta V$$

$$\Rightarrow C = \frac{1}{K} \frac{ab}{b-a}$$